

## 2SA965-Y(F,M)

#### 2SA965-Y(F,M) Information



Part Number	2SA965-Y(F,M)	
Manufacturer	Toshiba Semiconductor and Storage	
Category	Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single	
Description	TRANS PNP 800MA 120V TO226-3	
Package	TO-226-3, TO-92-3 Long Body	
	For the pricing/inventory/lead time, please contact us Website: https://www.heisener.com E-mail: salesdept@heisener.com	



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# For Reference Only

### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



### 2SA965-Y(F,M) Specifications

Manufacturer Part Number2SA965-Y(F,M)ManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V@ 50mA, 500mACurrent - Collector Cutoff (Max)800mA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM		
CategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V@ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120VHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageKTM	Manufacturer Part Number	2SA965-Y(F,M)
Transistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, IcIV @ 50mA, 500mACurrent - Collector Cutoff (Max)000nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Manufacturer	Toshiba Semiconductor and Storage
PackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Lc) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Category	Discrete Semiconductor Products
Series-Stries-Transistor TypePNPCurrent - Collector (Lo) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM		Transistors - Bipolar (BJT) - Single
Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageKSTM	Package	TO-226-3, TO-92-3 Long Body
Current - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVcc Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Series	-
Voltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Transistor Type	PNP
Yce Saturation (Max) @ Ib, IcIV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Yce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Current - Collector (Ic) (Max)	800mA
Current - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Voltage - Collector Emitter Breakdown (Max)	120V
DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Vce Saturation (Max) @ Ib, Ic	1V @ 50mA, 500mA
Power - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Current - Collector Cutoff (Max)	100nA (ICBO)
Frequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	DC Current Gain (hFE) (Min) @ Ic, Vce	80 @ 100mA, 5V
Operating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Power - Max	900mW
Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Frequency - Transition	120MHz
Package / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Operating Temperature	150°C (TJ)
Supplier Device Package LSTM	Mounting Type	Through Hole
	Package / Case	TO-226-3, TO-92-3 Long Body
Report errors <sup>6</sup>	Supplier Device Package	LSTM
Report crists.		Report errors?

#### 2SA965-Y(F,M) Guarantees



Quality Guarantees

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

# SERVICE BUARANTEE

#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

#### 2SA965-Y(F,M) Payment Methods





If you have any question about 2SA965-Y(F,M), please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com